L Number	Hits	Search Text	DB	Time stamp
-	71397	semiconductor and oxidation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 08:44
-	40285	(semiconductor and oxidation) and temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 08:46
-	11425	((semiconductor and oxidation) and temperature) and chamber	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 08:46
-	10744	(((semiconductor and oxidation) and temperature) and chamber) and (thermal heating annealing heat$2 anneal$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 08:48
-	835	((((semiconductor and oxidation) and temperature) and chamber) and (thermal heating annealing heat$2 anneal$4)) and ramp$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 08:49
-	744	(((((semiconductor and oxidation) and temperature) and chamber) and (thermal heating annealing heat$2 anneal$4)) and ramp$2) and rate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 10:27
-	535	((((((semiconductor and oxidation) and temperature) and chamber) and (thermal heating annealing heat$2 anneal$4)) and ramp$2) and rate) and cool$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 10:28
-	534	(((((((semiconductor and oxidation) and temperature) and chamber) and (thermal heating annealing heat$2 anneal$4)) and ramp$2) and rate) and cool$3) and (process processing method)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 10:28
-	27	((((((((semiconductor and oxidation) and temperature) and chamber) and (thermal heating annealing heat$2 anneal$4)) and ramp$2) and rate) and cool$3) and (process processing method)) and (stabilizing with temperature)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 08:56
-	518	((((((((semiconductor and oxidation) and temperature) and chamber) and (thermal heating annealing heat$2 anneal$4)) and ramp$2) and rate) and cool$3) and (process processing method)) and step$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 10:28
-	165	((((((((semiconductor and oxidation) and temperature) and chamber) and (thermal heating annealing heat$2 anneal$4)) and ramp$2) and rate) and cool$3) and (process processing method)) and ((stable stabilization) with temperature)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 08:56
-	187	((((((((semiconductor and oxidation) and temperature) and chamber) and (thermal heating annealing heat$2 anneal$4)) and ramp$2) and rate) and cool$3) and (process processing method)) and ((stable stabilization stabilizing) with temperature)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 10:29

-	179	(((((((((semiconductor and oxidation) and temperature) and chamber) and (thermal heating annealing heat$2 anneal$4)) and ramp$2) and rate) and cool$3) and (process processing method)) and ((stable stabilization stabilizing) with temperature)) and step$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 08:58
-	179	((((((((((semiconductor and oxidation) and temperature) and chamber) and (thermal heating annealing heat$2 anneal$4)) and ramp$2) and rate) and cool$3) and (process processing method)) and ((stable stabilization stabilizing) with temperature)) and step$4) and (up down)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 08:58
-	540	((((semiconductor and oxidation) and temperature) and chamber) and (thermal heating annealing heat$2 anneal$4)) and (ramp$3 with temperature)	USPAT; US-PGPUB	2003/03/31 10:26
-	545	((((semiconductor and oxidation) and temperature) and chamber) and (thermal heating annealing heat$2 anneal$4)) and (ramp$3 with temperature)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 10:27
-	473	(((((semiconductor and oxidation) and temperature) and chamber) and (thermal heating annealing heat$2 anneal$4)) and (ramp$3 with temperature)) and rate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 10:27
-	473	((((((semiconductor and oxidation) and temperature) and chamber) and (thermal heating annealing heat$2 anneal$4)) and (ramp$3 with temperature)) and rate) and rate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 10:27
-	333	(((((((semiconductor and oxidation) and temperature) and chamber) and (thermal heating annealing heat$2 anneal$4)) and (ramp$3 with temperature)) and rate) and rate) and cool$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 10:28
-	333	(((((((semiconductor and oxidation) and temperature) and chamber) and (thermal heating annealing heat$2 anneal$4)) and (ramp$3 with temperature)) and rate) and rate) and cool$3) and (process processing method)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 10:28
-	322	(((((((((semiconductor and oxidation) and temperature) and chamber) and (thermal heating annealing heat$2 anneal$4)) and (ramp$3 with temperature)) and rate) and rate) and cool$3) and (process processing method)) and step$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 10:29
-	97	((((((((((semiconductor and oxidation) and temperature) and chamber) and (thermal heating annealing heat$2 anneal$4)) and (ramp$3 with temperature)) and rate) and rate) and cool$3) and (process processing method)) and step$4) and ((stable stabilization stabilizing) with temperature)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 10:29